

Tao Tao

List of Publications by Year in descending order

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38
papers

508
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840776

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docs citations

39
times ranked

566
citing authors

#	ARTICLE	IF	CITATIONS
1	Three-dimensional monolithic micro-LED display driven by atomically thin transistor matrix. <i>Nature Nanotechnology</i> , 2021, 16, 1231-1236.	31.5	120
2	High Color Rendering Index Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes. <i>Advanced Functional Materials</i> , 2016, 26, 36-43.	14.9	58
3	Solar-blind ultraviolet photodetector based on vertically aligned single-crystalline $\text{In}^{2+}\text{Ga}_{2+}\text{O}_{3+}$ nanowire arrays. <i>Nanophotonics</i> , 2020, 9, 4497-4503.	6.0	35
4	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , 2020, 32, e1904354.	21.0	34
5	Significant improvements in InGaN/GaN nano-photoelectrodes for hydrogen generation by structure and polarization optimization. <i>Scientific Reports</i> , 2016, 6, 20218.	3.3	27
6	Manipulable and Hybridized, Ultralow-Threshold Lasing in a Plasmonic Laser Using Elliptical InGaN/GaN Nanorods. <i>Advanced Functional Materials</i> , 2017, 27, 1703198.	14.9	23
7	C-Plane Blue Micro-LED With 1.53 GHz Bandwidth for High-Speed Visible Light Communication. <i>IEEE Electron Device Letters</i> , 2022, 43, 910-913.	3.9	23
8	Investigations of Sidewall Passivation Technology on the Optical Performance for Smaller Size GaN-Based Micro-LEDs. <i>Crystals</i> , 2021, 11, 403.	2.2	19
9	Investigation of surface plasmon coupling with the quantum well for reducing efficiency droop in GaN-based light emitting diodes. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	14
10	1 W/mm Output Power Density for H-Terminated Diamond MOSFETs With $\text{Al}_{2+}\text{O}_{3+}/\text{SiO}_{2+}$ Bi-Layer Passivation at 2 GHz. <i>IEEE Journal of the Electron Devices Society</i> , 2021, 9, 160-164.	2.1	14
11	Asymmetric tunneling model of forward leakage current in GaN/InGaN light emitting diodes. <i>AIP Advances</i> , 2015, 5, 087151.	1.3	12
12	Spatially localised luminescence emission properties induced by formation of ring-shaped quasi-potential trap around V-pits in InGaN epi-layers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 2823-2827.	1.8	11
13	Investigation of surface-plasmon coupled red light emitting InGaN/GaN multi-quantum well with Ag nanostructures coated on GaN surface. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	10
14	Architectures and DFT calculations of polyrotaxane MOFs with nanoscale macrocycles. <i>Dalton Transactions</i> , 2016, 45, 3334-3339.	3.3	10
15	Single-crystal GaN layer converted from $\text{In}^{2+}\text{Ga}_{2+}\text{O}_{3+}$ films and its application for free-standing GaN. <i>CrystEngComm</i> , 2019, 21, 1224-1230.	2.6	10
16	Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. <i>Small</i> , 2020, 16, 1906205.	10.0	10
17	Growth and nitridation of $\text{In}^{2+}\text{Ga}_{2+}\text{O}_{3+}$ thin films by Sol-Gel spin-coating epitaxy with post-annealing process. <i>Journal of Sol-Gel Science and Technology</i> , 2021, 100, 183-191.	2.4	10
18	Polarized Emission From InGaN/GaN Single Nanorod Light-Emitting Diode. <i>IEEE Photonics Technology Letters</i> , 2016, 28, 721-724.	2.5	9

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19	1.26 W/mm Output Power Density at 10 GHz for Si ₃ N ₄ Passivated H-Terminated Diamond MOSFETs. IEEE Transactions on Electron Devices, 2021, 68, 5068-5072.	3.0	8
20	White-Light GaN-1/4LEDs Employing Green/Red Perovskite Quantum Dots as Color Converters for Visible Light Communication. Nanomaterials, 2022, 12, 627.	4.1	7
21	A Selective Etching Route for Large-Scale Fabrication of 1/2-Ga ₂ O ₃ Micro-/Nanotube Arrays. Nanomaterials, 2021, 11, 3327.	4.1	7
22	High-Performance Semi-Polar InGaN/GaN Green Micro Light-Emitting Diodes. IEEE Photonics Journal, 2020, 12, 1-7.	2.0	6
23	High Performance Wide Angle DBR Design for Optoelectronic Devices. IEEE Photonics Journal, 2021, 13, 1-6.	2.0	6
24	Observation and Modeling of Leakage Current in AlGaN Ultraviolet Light Emitting Diodes. IEEE Photonics Technology Letters, 2019, 31, 1697-1700.	2.5	4
25	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900729.	1.8	4
26	Epitaxial Growth and Characteristics of Nonpolar a-Plane InGaN Films with Blue-Green-Red Emission and Entire In Content Range. Chinese Physics Letters, 2022, 39, 048101.	3.3	4
27	Self-Assembly Nanopillar/Superlattice Hierarchical Structure: Boosting AlGaN Crystalline Quality and Achieving High-Performance Ultraviolet Avalanche Photodetector. ACS Applied Materials & Interfaces, 2022, 14, 33525-33537.	8.0	4
28	A High-Performance SiO ₂ /SiN _x 1-D Photonic Crystal UV Filter Used for Solar-Blind Photodetectors. IEEE Photonics Journal, 2019, 11, 1-7.	2.0	3
29	Improved Optical Properties of Nonpolar AlGaN-Based Multiple Quantum Wells Emitting at 280 nm. IEEE Photonics Journal, 2021, 13, 1-7.	2.0	3
30	Monolithic 3D μ -LED displays through BEOL integration of large-area MoS ₂ TFT matrix. , 2021, , .		2
31	Enhanced InGaN/GaN photoelectrodes for visible-light-driven hydrogen generation by surface roughening. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2704-2708.	1.8	1
32	Light-Emitting Diodes: High Color Rendering Index Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes (Adv. Funct. Mater. 1/2016). Advanced Functional Materials, 2016, 26, 156-156.	14.9	0
33	Lasers: Manipulable and Hybridized, Ultralow-Threshold Lasing in a Plasmonic Laser Using Elliptical InGaN/GaN Nanorods (Adv. Funct. Mater. 37/2017). Advanced Functional Materials, 2017, 27, .	14.9	0
34	23.3: Invited Paper: Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes. Digest of Technical Papers SID International Symposium, 2019, 50, 225-227.	0.3	0
35	Improved Performance of Hybrid Organic/Inorganic p-n Heterojunction White Light-Emitting Diodes with 4,4'-Cyclohexane-1,1'-diylbis[N,N-bis(4-methylphenyl)aniline] as a Multifunctional Hole Transport Layer. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900763.	1.8	0
36	Improved Performance of Hybrid Organic/Inorganic p-n Heterojunction White Light-Emitting Diodes with 4,4'-Cyclohexane-1,1'-diylbis[N,N-bis(4-methylphenyl)aniline] as a Multifunctional Hole Transport Layer. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2070029.	1.8	0

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37	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2070028.	1.8	0
38	46.4: Fabrication of InGaN/GaN-based nano-LEDs for display applications. <i>Digest of Technical Papers SID International Symposium</i> , 2021, 52, 568-568.	0.3	0